

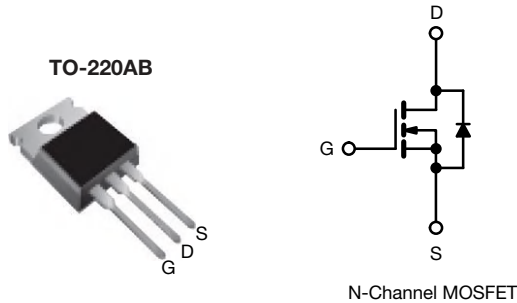
HM830-VB Datasheet

N-Channel 600V (D-S) Power MOSFET

PRODUCT SUMMARY	
V _{DS} (V)	600
R _{DS(on)} (Ω)	V _{GS} = 10 V 0.780
Q _g max. (nC)	49
Q _{gs} (nC)	13
Q _{gd} (nC)	20
Configuration	Single

FEATURES

- Low gate charge Q_g results in simple drive requirement
- Improved gate, avalanche and dynamic dV/dt ruggedness
- Fully characterized capacitance and avalanche voltage and current



APPLICATIONS

- Switch mode power supply (SMPS)
- Uninterruptible power supply
- High speed power switching

APPLICABLE OFF LINE SMPS TOPOLOGIES

- Active clamped forward
- Main switch

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	600	V	
Gate-Source Voltage		V _{GS}	± 30		
Continuous Drain Current	V _{GS} at 10 V	I _D	T _C = 25 °C	8.0	A
			T _C = 100 °C	5.8	
Pulsed Drain Current ^a		I _{DM}	37		
Linear Derating Factor			1.3	W/°C	
Single Pulse Avalanche Energy ^b		E _{AS}	290	mJ	
Repetitive Avalanche Current ^a		I _{AR}	8.0	A	
Repetitive Avalanche Energy ^a		E _{AR}	17	mJ	
Maximum Power Dissipation	T _C = 25 °C	P _D	170	W	
Peak Diode Recovery dV/dt ^c		dV/dt	5.0	V/ns	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	
Soldering Recommendations (Peak temperature) ^d	for 10 s		300		
Mounting Torque	6-32 or M3 screw		10	lbf · in	
			1.1	N · m	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- Starting T_J = 25 °C, L = 6.8 mH, R_g = 25 Ω, I_{AS} = 9.2 A (see fig. 12).
- I_{SD} ≤ 9.2 A, dI/dt ≤ 50 A/μs, V_{DD} ≤ V_{DS}, T_J ≤ 150 °C.
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	R_{thCS}	0.50	-	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.75	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$		600	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}$, $I_D = 1\text{ mA}$		-	660	-	mV/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$		2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 30\text{ V}$		-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$		-	-	25	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$		-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}$	$I_D = 5.5\text{ A}^b$	-	0.780	-	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 50\text{ V}, I_D = 5.5\text{ A}$		5.5	-	-	S
Dynamic							
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V},$ $V_{DS} = 25\text{ V},$ $f = 1.0\text{ MHz},$ see fig. 5		-	1400	-	pF
Output Capacitance	C_{oss}			-	180	-	
Reverse Transfer Capacitance	C_{rss}			-	7.1	-	
Output Capacitance	C_{oss}	$V_{GS} = 0\text{ V}$	$V_{DS} = 1.0\text{ V}, f = 1.0\text{ MHz}$	-	1957	-	pF
Effective Output Capacitance	$C_{oss\text{ eff.}}$		$V_{DS} = 480\text{ V}, f = 1.0\text{ MHz}$	-	49	-	
			$V_{DS} = 0\text{ V to } 480\text{ V}$	-	96	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}$	$I_D = 8.0\text{ A}, V_{DS} = 400\text{ V}$ see fig. 6 and 13 ^b	-	-	49	nC
Gate-Source Charge	Q_{gs}			-	-	13	
Gate-Drain Charge	Q_{gd}			-	-	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 300\text{ V}, I_D = 8.0\text{ A}$ $R_g = 9.1\text{ }\Omega, R_D = 35.5\text{ }\Omega,$ see fig. 10 ^b		-	13	-	ns
Rise Time	t_r			-	25	-	
Turn-Off Delay Time	$t_{d(off)}$			-	30	-	
Fall Time	t_f			-	22	-	
Gate Input Resistance	R_g	$f = 1\text{ MHz},$ open drain		0.5	-	3.2	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	9.2	A
Pulsed Diode Forward Current ^a	I_{SM}			-	-	37	
Body Diode Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 8.0\text{ A}, V_{GS} = 0\text{ V}^b$		-	-	1.5	V
Body Diode Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = 8.0\text{ A}, di/dt = 100\text{ A}/\mu\text{s}^b$		-	530	800	ns
Body Diode Reverse Recovery Charge	Q_{rr}			-	3.0	4.4	μC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)					

Notes

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width $\leq 300\text{ }\mu\text{s}$; duty cycle $\leq 2\%$.
- c. $C_{oss\text{ eff.}}$ effective is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

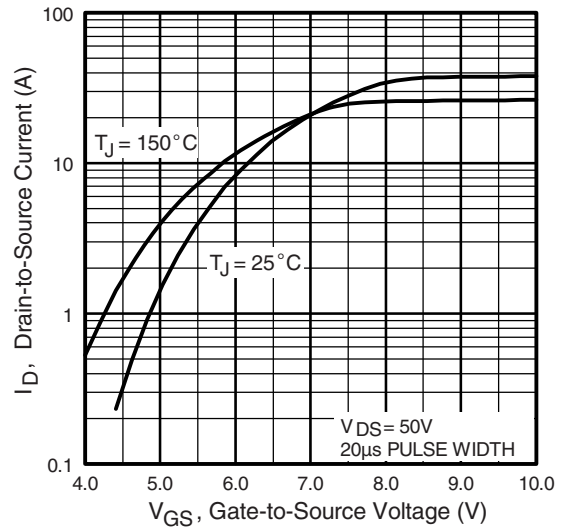




Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



Fig. 8 - Maximum Safe Operating Area



Fig. 9 - Maximum Drain Current vs. Case Temperature



Fig. 10a - Switching Time Test Circuit



Fig. 10b - Switching Time Waveforms



Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

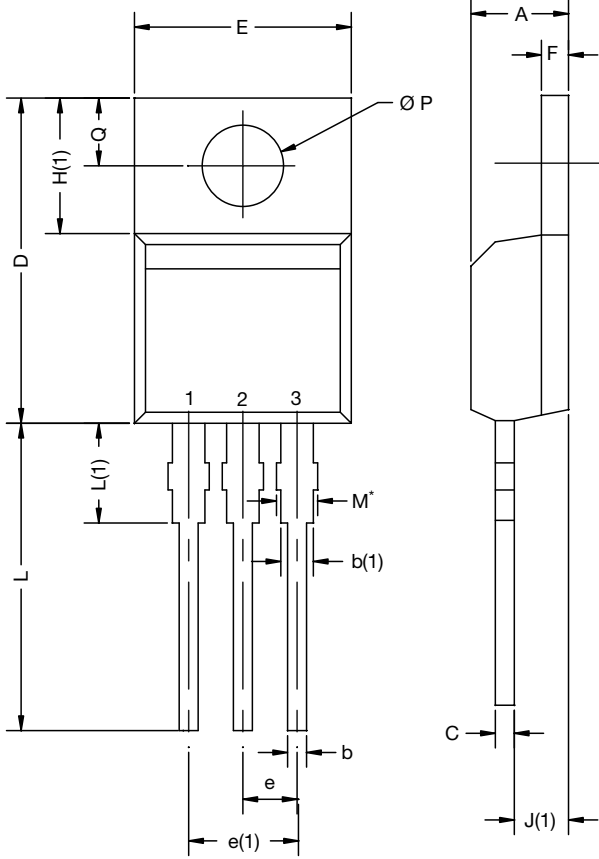
Peak Diode Recovery dV/dt Test Circuit



Note
a. $V_{GS} = 5 V$ for logic level devices

Fig. 14 - For N-Channel

TO-220AB



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
$\varnothing P$	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15
DWG: 6031

Note

- M^* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

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